

AON4602

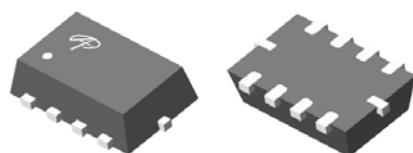
Complementary Enhancement Mode Field Effect Transistor

General Description

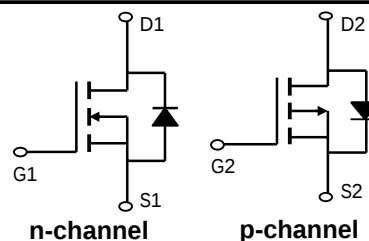
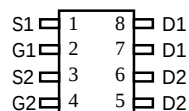
The AON4602 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. Standard Product AON4602 is Pb-free (meets ROHS & Sony 259 specifications). AON4602L is a Green Product ordering option. AON4602 and AON4602L are electrically identical.

Features

n-channel	p-channel	
$V_{DS} (V) = 20V$	-20V	
$I_D = 4.2A$	-3.4A	($V_{GS} = \pm 4.5V$)
$R_{DS(ON)} < 50m\Omega$	$< 90m\Omega$	($V_{GS} = \pm 4.5V$)
$R_{DS(ON)} < 63m\Omega$	$< 120m\Omega$	($V_{GS} = \pm 2.5V$)
$R_{DS(ON)} < 87m\Omega$	$< 160m\Omega$	($V_{GS} = \pm 1.8V$)



DFN3X2



Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 8	± 8	V
Continuous Drain Current ^A	I_D	4.2	-3.4	A
$T_A = 25^\circ C$				
$T_A = 70^\circ C$		3.2	-2.7	
Pulsed Drain Current ^B	I_{DM}	15	-15	
Power Dissipation	P_D	1.4	1.7	W
		0.9	1.1	
$T_A = 25^\circ C$				
$T_A = 70^\circ C$				
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	100	125	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	63	80	$^\circ C/W$
Steady-State				

Thermal Characteristics: p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	49	75	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	81	100	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	37	45	$^\circ C/W$
Steady-State				

n-channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.4	0.7	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}$, $I_D=4.2\text{A}$ $T_J=125^{\circ}\text{C}$		41 58	50 70	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=3.7\text{A}$		52	63	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$, $I_D=3.2\text{A}$		67	87	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4.2\text{A}$		11		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.8	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, $f=1\text{MHz}$		436		pF
C_{oss}	Output Capacitance			66		pF
C_{rss}	Reverse Transfer Capacitance			44		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=10\text{V}$, $I_D=4.2\text{A}$		6.2		nC
Q_{gs}	Gate Source Charge			1.6		nC
Q_{gd}	Gate Drain Charge			0.5		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=5\text{V}$, $V_{DS}=10\text{V}$, $R_L=2.7\Omega$, $R_{GEN}=6\Omega$		5.5		ns
t_r	Turn-On Rise Time			6.3		ns
$t_{D(off)}$	Turn-Off Delay Time			40		ns
t_f	Turn-Off Fall Time			12.7		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		12.3		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		3.5		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $\leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$.

The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

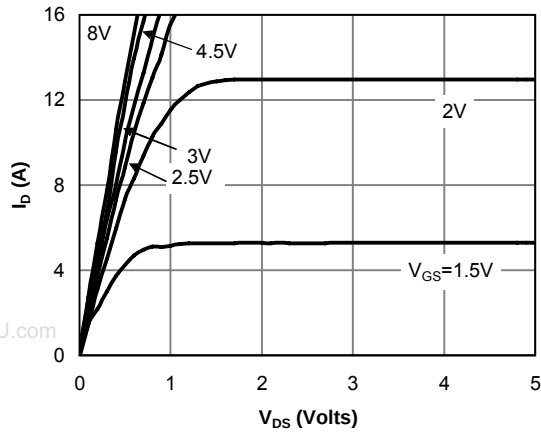


Fig 1: On-Region Characteristics

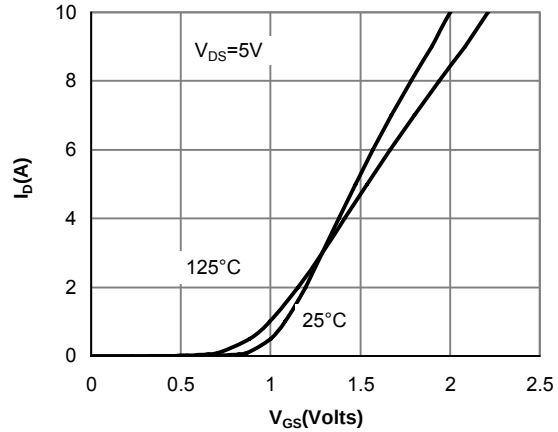


Figure 2: Transfer Characteristics

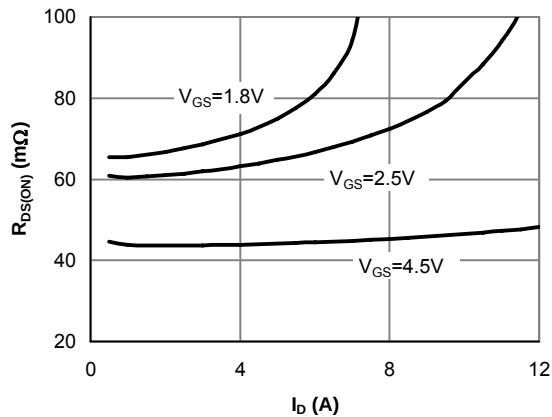


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

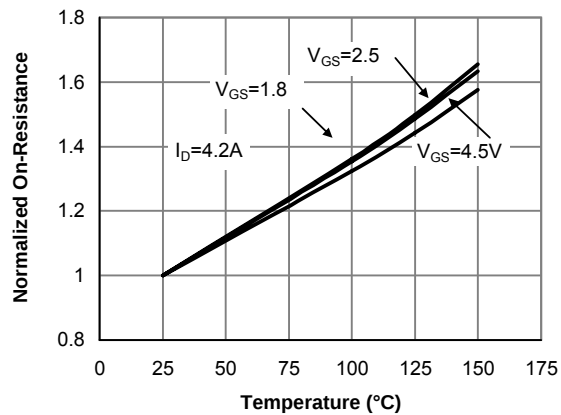


Figure 4: On-Resistance vs. Junction Temperature

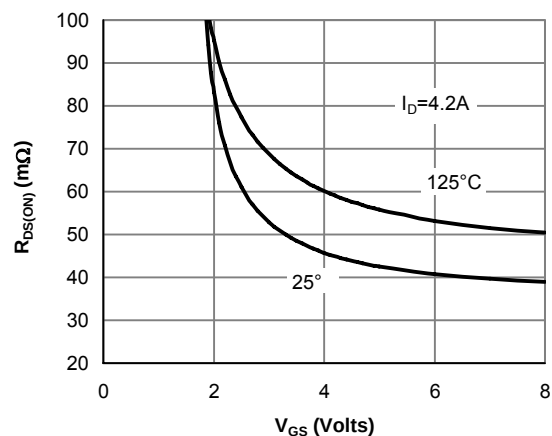


Figure 5: On-Resistance vs. Gate-Source Voltage

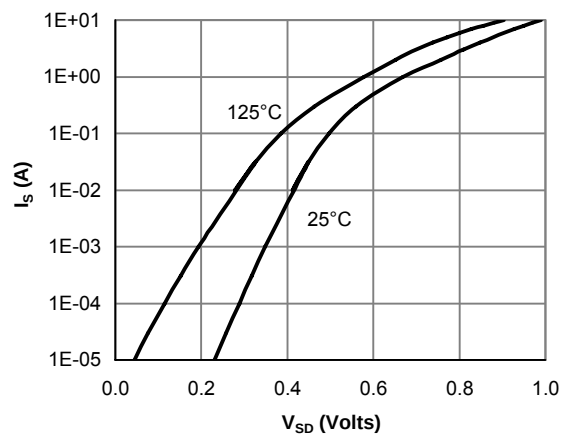


Figure 6: Body-Diode Characteristics

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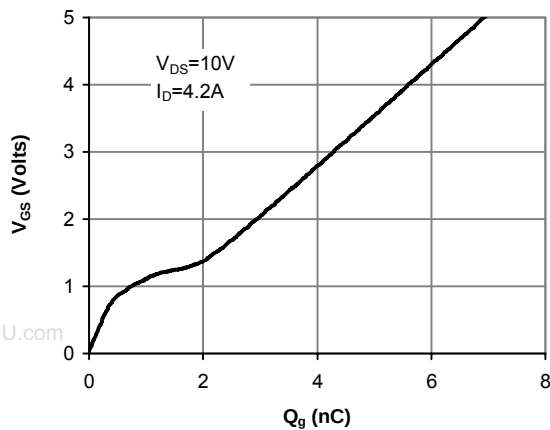


Figure 7: Gate-Charge Characteristics

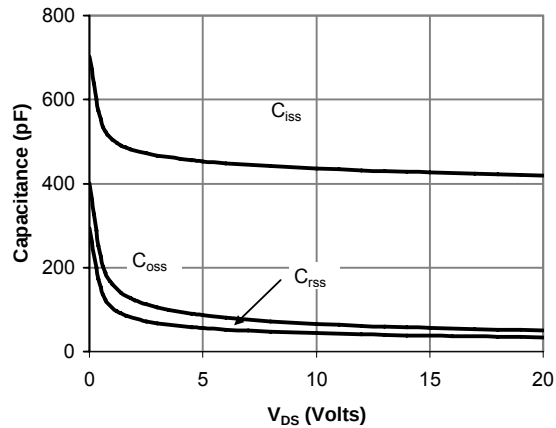


Figure 8: Capacitance Characteristics

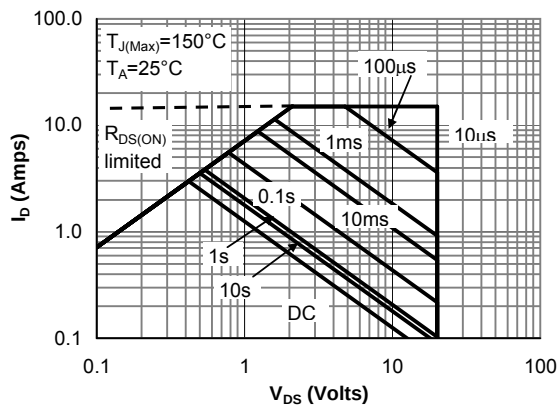


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

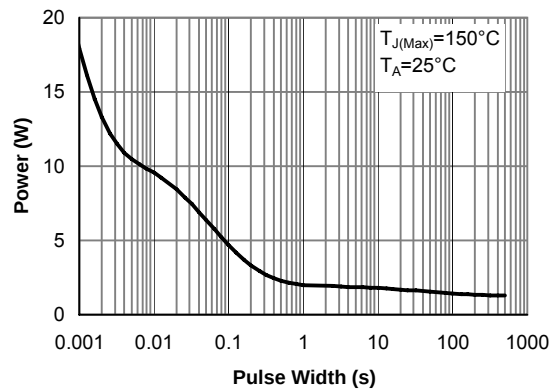


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

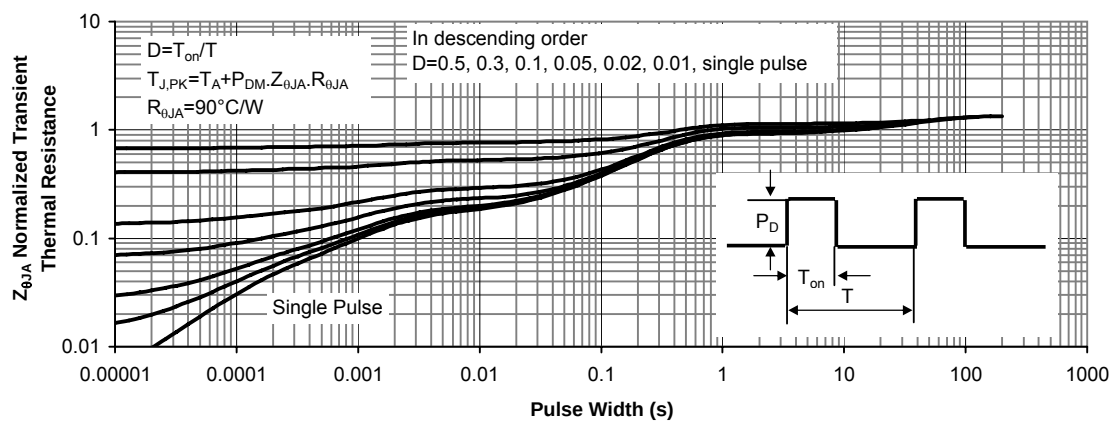


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics (T=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu A$, $V_{GS} = 0V$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16V$, $V_{GS} = 0V$ $T_J = 55^\circ C$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0V$, $V_{GS} = \pm 8V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	-0.3	-0.63	-1	V
$I_{D(ON)}$	On state drain current	$V_{GS} = -4.5V$, $V_{DS} = -5V$	-15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_D = -3.4A$ $T_J = 125^\circ C$		73 102	90 125	$m\Omega$
		$V_{GS} = -2.5V$, $I_D = -2.5A$		95	120	$m\Omega$
		$V_{GS} = -1.8V$, $I_D = -1.5A$		123	160	$m\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = -5V$, $I_D = -3.4A$	4	7		S
V_{SD}	Diode Forward Voltage	$I_S = -1A$, $V_{GS} = 0V$		-0.83	-1	V
I_S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS} = 0V$, $V_{DS} = -10V$, $f = 1MHz$		540		pF
C_{oss}	Output Capacitance			72		pF
C_{rss}	Reverse Transfer Capacitance			49		pF
R_g	Gate resistance	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$		12		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = -3.8A$		6.1		nC
Q_{gs}	Gate Source Charge			0.6		nC
Q_{gd}	Gate Drain Charge			1.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $R_L = 2.6\Omega$, $R_{GEN} = 3\Omega$		10		ns
t_r	Turn-On Rise Time			12		ns
$t_{D(off)}$	Turn-Off DelayTime			44		ns
t_f	Turn-Off Fall Time			22		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F = -3.8A$, $dI/dt = 100A/\mu s$		21		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F = -3.8A$, $dI/dt = 100A/\mu s$		7.5		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The SOA curve provides a single pulse rating.

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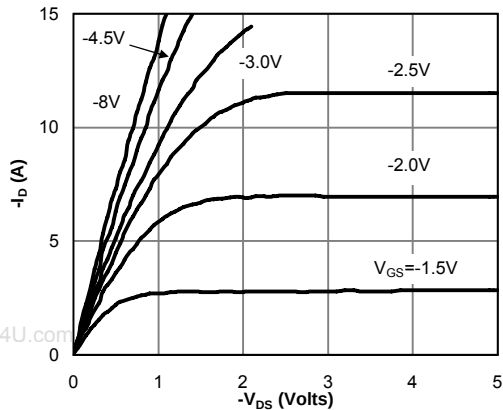


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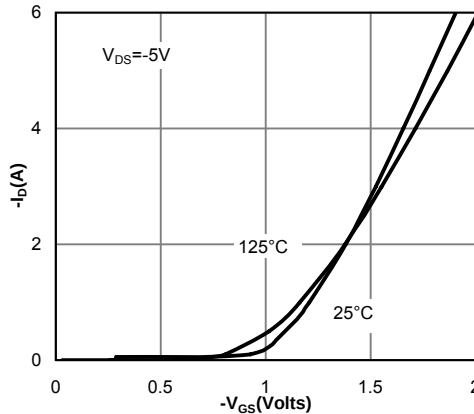


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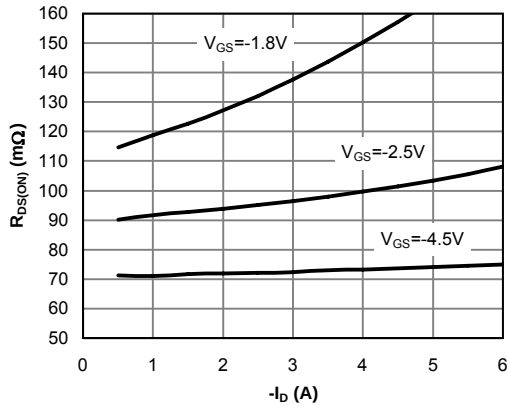


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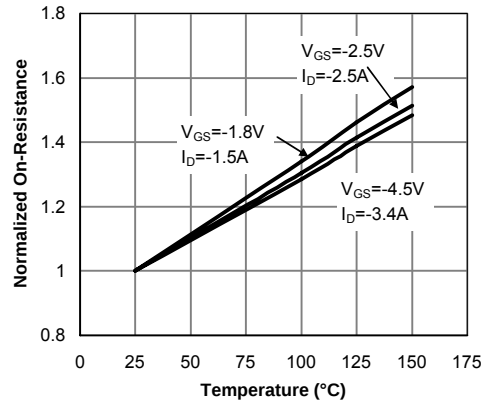


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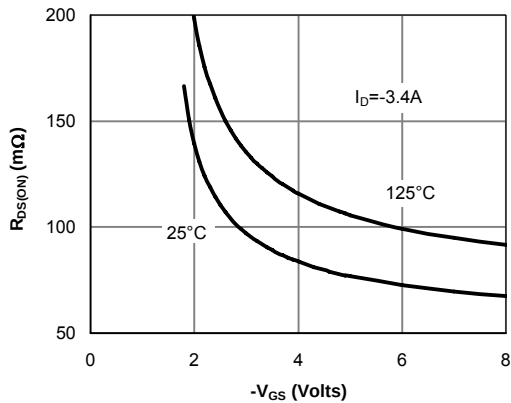


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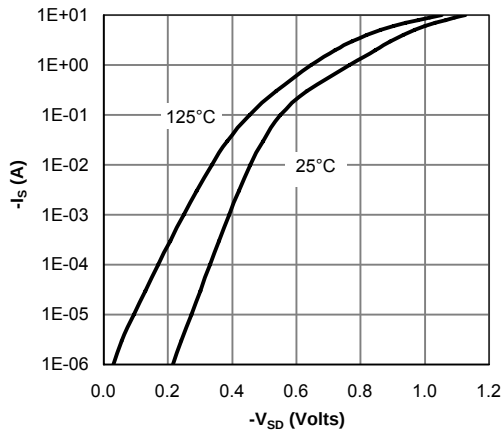


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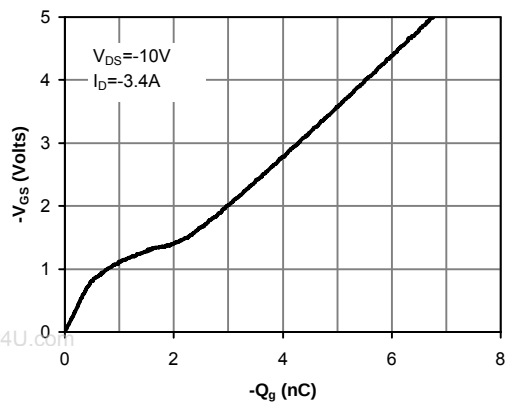


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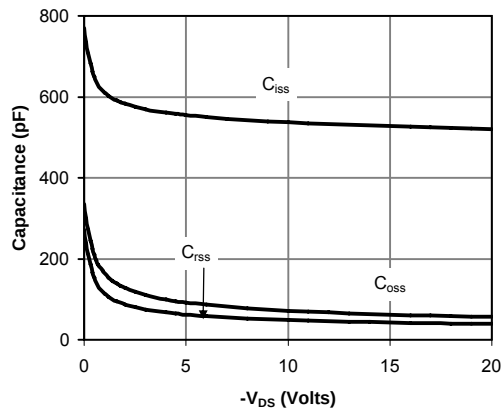


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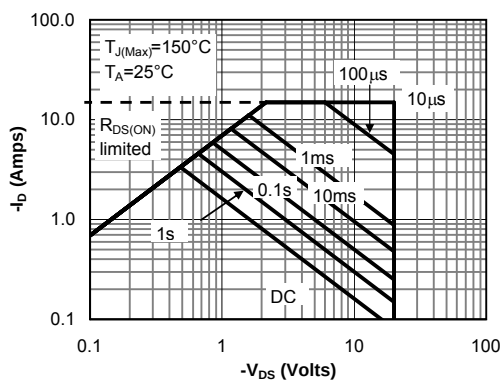


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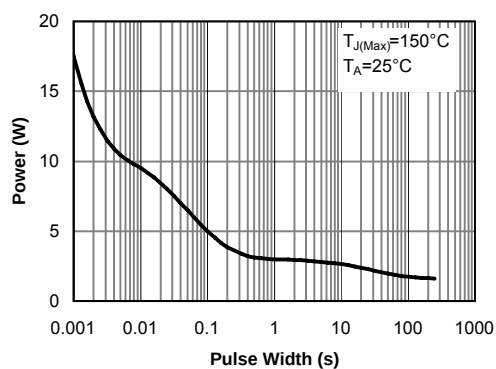


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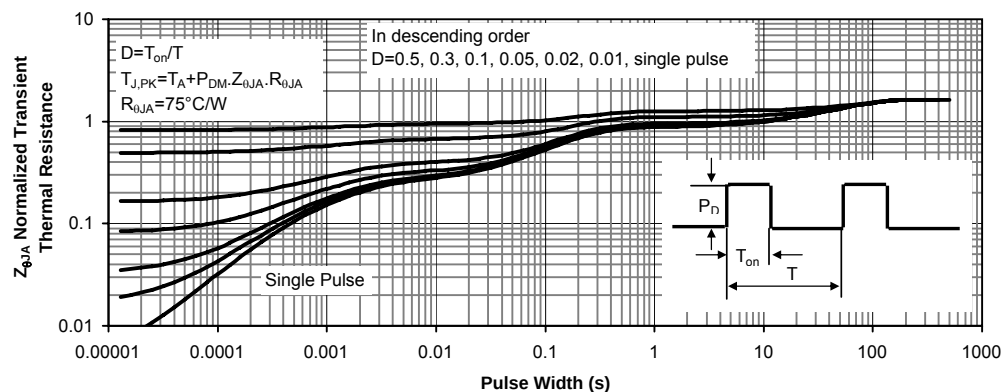


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